The Crystal Structure of SnP₃ and a Note on the Crystal Structure of GeP₃

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Received April 3, 1972

SnP₃ crystallizes in the trigonal space group $R\overline{3}m$ with six formula units in a unit cell of dimensions a = 7.378 Å and c = 10.512 Å. The detailed atomic arrangement has been determined from three-dimensional single crystal X ray data.

The structure is characterized as a layer structure related to the As-type structure (A7). The identical layers consist of puckered P6 rings connected by Sn atoms. The centers of the P6 rings are situated between Sn atoms of adjacent layers. This leads to a distorted octahedral coordination for the tin atoms with three phosphorus atoms belonging to the same layer as the tin atom at a distance of 2.662 Å, and three phosphorus atoms in an adjacent layer at a distance of 2.925 Å. The P-P bond length within the rings is 2.222 Å and the P-P-P bond angle is 99.1°.

Introduction

One of the present authors (1) has reported powder data for $Sn_{0.3}P$. This phase has now been further studied by single crystal X-ray diffraction methods and it has been found that the ideal crystallographic formula is SnP₃. In Ref. 1 it was also noted that X-ray powder data given by Donohue and Young (6) for GeP₃ indicated that the high pressure phase GeP₃ probably has the same structure as SnP₃. This has now been confirmed by a least-squares refinement of the powder data from Ref. 6.

Experimental

Preparation. The synthesis was performed in two stages as described in Ref. 1. The nominal composition was SnP₄ and the final heat treatment was undertaken for 2 days at 575°C followed by slow cooling to room temperature. The sample so obtained had a silicon-like appearance (2) with visible traces of red phosphorus.

X-ray investigation. Phase analysis and a determination of the unit cell dimensions was carried out by X-ray powder methods using a Guinier-Hägg focussing camera with $CuK\alpha_1$ radiation. Silicon (a = 5.43054 Å) was used as an internal standard. The single crystal investigation Copyright © 1972 by Academic Press, Inc. All rights of reproduction in any form reserved.

was performed with the equi-inclination Weissenberg method using zirconium-filtered MoK radiation and the multiple film technique. Thin iron foils were interleaved between successive films. The intensities were estimated visually by comparison with a calibrated intensity scale. The intensities were corrected for Lorentz and polarization factors. Atomic scattering factors and the real part of the anomalous dispersion correction were taken from Ref. 3.

The calculations were carried out in part on an IBM 1800 computer and partly on a CDC 3600 computer using the programs CELSIUS, DRF, LALS, and DISTAN. The programs have been described briefly elsewhere (4).

Determination and Refinement of the SnP₃ Structure

The single crystal used was very irregular in shape. It was therefore considered that an attempt to correct for absorption would hardly provide any significant improvement in the intensity data. The errors due to absorption are furthermore rather small due to the smallness of the crystal, which measured less than $0.04 \times$ 0.06×0.10 mm [μ (MoK α) = 61 cm⁻¹]. The crystal was rotated about the [100] direction in the nonprimitive hexagonal unit cell which will

be used in the following. Only general reflexions with -h + k + l = 3n were observed indicating a rhombohedral lattice. No special conditions were observed, and as no condition limiting the occurrence of special reflexions could be found. translational elements of symmetry could be excluded. The Laue symmetry was found to be $\overline{3}m$; there are therefore three possible space groups: R32, R3m and $R\overline{3}m$. The structure was determined on the basis of the nonprimitive hexagonal unit cell and it could be shown that all vectors in the Patterson projection P(V, W)could be explained by six tin atoms in the 6(c)position and eighteen phosphorus atoms in the 18(h) position. Comparison of electron densities based on calculated and observed structure factors respectively confirmed the proposed structure and gave improved positional parameters and scale factors. These values were then used in a least-squares refinement. The parameters refined were atomic coordinates, individual isotropic temperature factors and three scale factors, one for each of the three layer lines (0kl), (1kl) and (2kl). The weighting scheme of Cruickshank et al. (5), $w = 1/(a + |F_0| + c|F_0|^2 + c|F_0|^2)$ $d|F_0|^3$), was used with the values a = 70, c = 0.007, and d = 0.0001. The refinement was stopped when the discrepancy factor $R = \sum ||F_0| - |\hat{F_c}|| / \sum |F_0|$ was 0.093 for the 245 independent F values. The final structural description of SnP₃ is as follows: Space group $R\overline{3}m$ (D_{3d}^{5}); Hexagonal cell with a = 7.3785(5) Å; c = 10.5125(11) Å; U = 495.65Å³; Z = 6. Calculated density: 4.25 g cm⁻³. The atoms are in the 6(c) and the 18(h) positions with the parameter values:

Atom	x	У	Z	$B(Å^2)$
Sn 6(c)	0	0	0.2576(1)	0.45(8)
P 18(<i>h</i>)	0.5139(4)	0.4861(4)	0.2828(3)	0.56(8)

The limits of error given for the atomic parameters are the standard deviations obtained from the least-squares refinement. Interatomic distances and bond angles are given in Table I and observed and calculated structure factors in Table II.

Refinement of the GeP₃ Structure

The powder diffraction intensities of GeP_3 published by Donohue and Young (6) were corrected for Lorentz and polarization factors and used for computing the Patterson section P(0, V, W). This gave approximate starting

TABLE I

INTERATOMIC DISTANCES (Å UNITS) AND ANGLES WITH STANDARD DEVIATIONS IN SnP_3 . Distances Shorter than 3.3 Å are Listed			
Sn-3P	2.662(3)		
3P	2.925(3)		
P–2P	2.222(4)		
P-Sn-P	70.65(8)		
P-Sn-P	94.69(4)		
P-Sn-P	97.31(13)		
PSnP	161.78(12)		
Sn-P-Sn	161.78(12)		
Sn-P-P	98.21(13)		
Sn-P-P	93.57(12)		
PP-P	99.08(22)		

coordinates for a least-squares refinement. The final coordinates obtained from the refinement were, for Ge: [0, 0, 0.269(5)] and for P: [0.515(8), 0.485(8), 0.282(5)]. Standard deviations of atomic coordinates are given in parentheses. The discepancy factor as defined above is 0.136.

Description and Discussion of the SnP₃ Structure

 SnP_3 represents a new structure type, the main features of which have been predicted by Donohue and Young for the isostructural GeP_3 (6). The structure of SnP₃ can be described as a layer structure related to the As-type structure in which the corrugated layers are composed of puckered P_6 rings as shown in Fig. 1. The layers thus formed are stacked upon one another perpendicular to the c axis so that a distorted octahedral environment of phosphorus atoms is formed around each of the tin atoms. Hence, the tin atoms have six phosphorus neighbors; three within the layer at a distance of 2.662(3) Å and three in an adjacent layer at a distance of 2.925(3) Å. The corresponding distances in GeP₃ are 2,50(5) and 2,85(6).

Phosphorus has been reported to have the As type structure above 50 kbars (9). The cell dimensions of this form are a = 3.3777 Å and c = 8.806 Å. The distance corresponding to the hexagonal *a* axis of the As-type phosphorus can be found in the P₆ rings of SnP₃. This distance was found to be 3.382(4) Å.

In a recent survey of metal polyphosphides (7), a simple formula was derived for calculating the oxidation number of the metal atoms in poly-



Observed and Calculated Structure Factors (×10). Reflexions not Included in the Refinement are Marked with an Asterisk.

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FIG. 1. The atomic arrangement in a puckered layer of SnP₃. Small circles represent phosphorus atoms and large circles represent tin atoms.

phosphides. In a purely formalistic way polyphosphides were considered to be formed through a partial breaking down of the phosphorus network in elementary phosphorus. The metal atoms donate electrons to the phosphorus atoms, thus creating unshared electron pairs on the phosphorus atoms instead of electron pairs shared between them. These unshared pairs can then be used in bonding with the metal atoms. By considering the number and type of the different crystallographic positions occupied by phosphorus in a particular structure, it is possible to calculate an average value, $N_{\rm P}$, for the number of phosphorus neighbors per phosphorus atom in the structure. Since this number is 3 for elementary phosphorus and it was shown (7) to be always less than 3 in polyphosphides, $(3 - N_{\rm P})$ gives the number of P-P bonds which have to be broken per phosphorus atom to form the phosphorus network in the polyphosphide. In order to retain an electron octet on phosphorus, two electrons must be supplied to the phosphorus atoms for each severed P-P bond:

$$P = P + 2e^{-} \longrightarrow P + P + P$$

i.e., one electron per atom or, if $(3 - N_P)$ bonds are broken per atom, $(3 - N_P)$ electrons per atom. If X_P denotes the number of phosphorus atoms in a formula unit, $X_P(3 - N_P)$ is the number of electrons that have to be supplied to the phosphorus network per formula unit. If there are no metal-metal bonds in the structure, the average oxidation number for the metal atoms is then given by: $(X_P/X_{Me})(3 - N_P)$, where X_{Me} is the number of metal atoms per formula unit. In the case of SnP_3 the application of this rule is particularly simple since there is only one crystallographic position for the phosphorus atoms, each atom having two phosphorus neighbors.

By inserting the appropriate values $X_{\rm P} = 3$, $X_{\rm Sn} = 1$ and $N_{\rm P} = 2$ in the formula, an oxidation number of 3 is obtained for tin in SnP₃. Although an oxidation number which deviates from the group number is not unique for nontransition metal polyphosphides (7, 8), a value of 3 for tin is quite unexpected. Since there is only one crystallographic position for the tin atoms in SnP₃, it would seem hardly likely that the unusual oxidation number 3 results from the simultaneous existence of tin atoms having the more usual oxidation numbers 2 and 4 in equal proportions. However, the oxidation number 3 appears more reasonable on considering the part played by tin in the structure. It has been pointed out above that the SnP_3 structure type is related to the A7, arsenic-type structure. By systematically replacing every fourth atom in an arsenic layer by tin and the rest by phosphorus, the SnP₃ structure is obtained. That is to say, tin plays structurally the same rôle as phosphorus, and in order to explain the A7type structure, every atom has to contribute three electrons to the covalent bonding system. A similar situation seems to occur in the cubic and tetragonal high-pressure forms of SnP (10) and oxidation number 3 for germanium has been proposed for the tetragonal high-pressure forms of GeP and GeAs (6).

If the interpretation of the SnP_3 structure type given above is accepted, the fourth valence electron from tin still remains to be accounted for. It seems probable that this electron, instead of being localized on the tin atoms, goes into a conduction band. There are as yet no reliable data available on the electrical conductivity of SnP_3 , but for the isostructural GeP₃ resistivity measurements indicate metallic conductivity (6). The physical properties of SnP_3 are presently the subject of studies by resistivity, magnetic susceptibility and Mössbauer spectroscopic measurements, and the results will be reported later.

Acknowledgments

The authors wish to thank Professor S. Rundqvist for his kind interest in this work and for much valuable advice. The authors are indebted to Dr. J. Thomas for the revision of the English text. The work has been supported financially by the Swedish Natural Science Research Council.

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